L Number	Hits	Search Text	DB	Time stamp
1	0	@ad<=20011206 and 'O' adjl 'SiON' adjl 'N' adjl 'SiON' adjl 'O'	USPAT; US-PGPUB; EPO; JPO;	2003/11/24 13:56
2	0	@ad<=20011206 and 'O/SiON/N/SiON/O'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/24
3	1	@ad<=20011206 and 'O-SiON-N-SiON-O'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/24 13:56
-	696	(438/400).ccls. and @ad<=20011206	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 11:22
-	6	((438/400).ccls. and @ad<=20011206) and ONO	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17
-	0	@ad<=20011206 and 'ONO structure' with 'buffer layer'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/24
-	290	@ad<=20011206 and 'ONO structure'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/24
-	160	@ad<=20011206 and 'Oxide' with 'SiON' with 'SiN' with 'SiON' with 'Oxide'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17
-	3	@ad<=20011206 and 'ONO structure' and 'buffer layer'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:40
-	1	@ad<=20011206 and 'multi dielectric layer' and 'memory'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:43
-	26	@ad<=20011206 and 'multi' adj 'dielectric' and 'memory'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/24 11:47
-	0	@ad<=20011206 and 'O-SiON-N-SiON-O'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17 12:49
-	1393	@ad<=20011206 and oxide and SiON and Nitride and SiON and oxide	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17
-	0	@ad<=20011206 and oxide adj SiON adj Nitride adj SiON adj oxide	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:56
	atory 1	1/24/02 2:25:07 PM Pogo 1	IBM TDB	

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Γ	7 200	[0-14 20011206] [T 0 0 0 0 / 1 0 / 0 / 0 / 0 / 0 / 0 / 0 /
-	300	<pre>@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide'</pre>	USPAT;	2003/11/24
		with interide, with islow, with loxide,	US-PGPUB;	11:28
			EPO; JPO; DERWENT;	
			IBM TDB	
-	107	(@ad<=20011206 and 'oxide' with 'SiON'	USPAT;	2003/06/19
	ļ	with 'nitride' with 'SiON' with 'oxide')	US-PGPUB;	14:52
		and memory	EPO; JPO;	
		-	DERWENT;	
			IBM TDB	
-	540	@ad<=20011206 and (438/778).ccls.	USPĀT;	2002/05/17
1			US-PGPUB;	14:32
			EPO; JPO;	
l .			DERWENT;	\ \ \
			IBM_TDB	
-	2862	((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
1		or (438/794) or (438/400) or	US-PGPUB;	08:49
		(438/769-770) or (438/770) or	EPO; JPO;	
	1	(438/775)).CCLS.	DERWENT;	
1_	2356	((257/324) or (257/314-315) or (257/406)	IBM_TDB	2002/11/24
}	2336	or (257/410)).CCLS.	USPAT; US-PGPUB;	2003/11/24 11:50
		(10//110//.0010.	EPO; JPO;	11.50
			DERWENT;	
			IBM TDB]
-	7	(((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
	1	or (438/794) or (438/400) or	US-PGPUB;	08:59
	1	(438/769-770) or (438/770) or	EPO; JPO;	
ì		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	1
		'silane' with 'nitrogen oxide'	IBM TDB	
-	6328	(((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
		or (438/794) or (438/400) or	US-PGPUB;	09:03
		(438/769-770) or (438/770) or	EPO; JPO;	
	1	(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
t		'SiON' or 'silicon oxynitride'	IBM_TDB	
] -	0	(((10 -)	USPAT;	2002/10/28
	l	or (438/794) or (438/400) or	US-PGPUB;	09:04
		(438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and	EPO; JPO; DERWENT;	
		SiH4 with N20 with NH3	IBM TDB	
_	8		USPAT;	2002/10/28
		or (438/794) or (438/400) or	US-PGPUB;	09:09
		(438/769-770) or (438/770) or	EPO; JPO;	""
	}	(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
1	1	'SiON' with 'deposition'	IBM TDB	
-	448	(((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
		or (438/794) or (438/400) or	US-PGPUB;	09:11
1		(438/769-770) or (438/770) or	EPO; JPO;	
		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
		'ammonia'	IBM_TDB	
-	190	(((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
		or (438/794) or (438/400) or	US-PGPUB;	09:11
		(438/769-770) or (438/770) or	EPO; JPO;	
		(438/775)).CCLS.) and @ad<=20011206 and 'ammonia' and 'silane'	DERWENT;	
_	194	@ad<=20011206 and 'ammonia' and 'silane'	IBM_TDB	2002/10/28
	154	and 'nitrogen oxide'	USPAT; US-PGPUB;	09:16
]	and interogen oxide	EPO; JPO;	1 03.10
			DERWENT;	
Į i			IBM TDB	
[-	359	@ad<=20011206 and 'oxide' with 'SiON'	USPAT;	2003/02/13
		with 'nitride' with 'SiON' with 'oxide'	US-PGPUB;	13:27
]			EPO; JPO;	
ĺ	[DERWENT;	
]			IBM_TDB	
-	27		USPAT;	2002/10/28
		same 'nitrogen oxide'	US-PGPUB;	09:19
			EPO; JPO;	
!			DERWENT;	
			IBM_TDB	L

- 0	-	0	@ad<=20011206 and 'oxide' same 'silane'	USPAT;	2003/02/13
- 0				US-PGPUB;	13:29
Bad<=20011206 and 'silane' same 'dichloro silane' with 'nitrogen oxide' SEPOLY SPECTURE SEPOLY S			oxide'		
0 @ad<-20011206 and 'silane' same 'dichloro USPAT; USPGUB; EPO. JPO DERWENT; EMPLOY USPAT; USPAT					
			0.14.00011006		
Property	-	0			
- 3			silane with 'nitrogen oxide'		13:30
3 8ad<-20011206 and 'silane' same 'dichlorosilane' with 'N.sub.20' SPAT; US-FOFUB; 13:36					
3 8ad<-20011206 and 'silane' same 'silane' same 'silane' same 'silane' same 'nitrous oxide' same 'silane' same 'silan		i			
dichlorosilane' with 'N.sub.20'		,	02d<-20011206 and Isilanal arms		2002/02/12
- 0 @ad<-20011206 and 'silicon oxide' same 'silane' same 'DCS' same 'N. sub.20' US-FGPUB; 13:37 EPG, JPO; DERWENT; IRM TDB USPAT; 13:37 EPG, JPO; DERWENT; IRM TDB USPAT; 13:39 US-FGPUB; 10:17 EPG, JPO; DERWENT; IRM TDB US-FGPUB; 10:17 EPG, JPO; DERWENT; IRM TDB US-FGPUB; 10:17 EPG, JPO; DERWENT; IRM TDB US-FGPUB; 10:51 US-FGPUB; 10:51 US-FGPUB; 10:29 US-FGPUB; 10:29 US-FGPUB; 10:37 EPG, JPO; DERWENT; IRM TDB US-FGPUB; 10:303/06/19 US-FGPUB; 10:37 EPG, JPO; DERWENT; IRM TDB US-FGPUB; 10:303/06/19 US-FGPUB; 10:303/]	Jan		
- 0			dichiologitane with N.Sub.20		13:36
0					
0 @ad<=20011206 and 'silicon oxide' same USPĀT; USPĀGUB; EPO; JPO; DERWENT; IBM TDB USPĀT; USPĀGUB; EPO					
Silane' same 'DCS' same 'N.sub.20' US-PGPUB; EPG/ JPG/ DERWENT; IBM TDB USPAT; US	_	0	@ad<=20011206 and 'silicon oxide' same		2003/02/13
- 32 @ad<=20011206 and 'silicon oxide' same 'silane' same 'N.sub.20'		_			
- 32					
Bad<-20011206 and 'silicon oxide' same 'siport before the company of the compan					
- 32					
Sead	-	32	@ad<=20011206 and 'silicon oxide' same		2003/02/13
- 25			'silane' same 'N.sub.20'		
25		ŀ		EPO; JPO;	
25 @ad<=20011206 and 'silicon oxide' same		1		DERWENT;	
'silane' same 'nitrous oxide' and 'dichlorosilane' US-PGPUB; EDO, JPO; DERWENT; IRM TDB USPAT; US-PGPUB; SPO, JPO; DERWENT; IRM TDB USPAT; US-PGPUB; SPO				IBM_TDB	
'dichlorosilane'	-	25		USPAT;	2003/06/19
- 71		1		US-PGPUB;	10:17
TIM TDB Same 'nitrous oxide' same 'silane' Same 'nitrous oxide' same 'silane' Same 'nitrous oxide' same Same 'nitrous oxide' same 'n			'dichlorosilane'	EPO; JPO;	
Sead<-20011206 and 'oxide' same 'silane' USPĀT, same 'nitrous oxide' same 'silane' USPĀT, same 'nitrous oxide' same USPĀT, same 'nitrous oxide' same USPĀT, same 'siH.sub.20' same USPĀT, same 'siH.sub.20' same USPĀT, same 'siH.sub.20' same USPĀT, same 'siH.sub.20' same USPĀT, same 'siH.sub.4' same 'n.sub.20' same USPĀT, same 'siH.sub.4' same 'n.sub.20' same 'siH.sub.4' same 'n.sub.20' same 'siH.sub.4' same 'n.sub.20' same 'siH.sub.4' same 'n.sub.20' same 'siH.sub.20' same 'nitrous oxide' same 'siH.sub.20' same		1		DERWENT;	
Same 'nitrous oxide' same				_	
'dichlorosilane' Cad<=20011206 and 'oxide' same	-	71			1
- 12					10:51
- 12 @ad<=20011206 and 'oxide' same 'SiH.sub.4' same 'N.sub.20' same USPĀT; US-FGPUB; EPO, JPO; DERWENT; IBM TDB USPĀT; US-FGPUB; EPO, JPO; DERWENT; IBM T			'dichlorosilane'		
12					
SiH.sub.4' same 'N.sub.20' same)	
SiH.sub.2Cl.sub.2'	-	12			
- 4 @ad<=20011206 and 'silicon oxide' same 'IBM_TDB USPAT; ISM_SUB.2Cl. sub.2' SiH. sub.4' same 'N. sub.2O' same 'SiH. sub.2Cl. sub.2' SiH. sub.2Cl. s					10:29
TEM_TDB USPAT;	1		'SiH.sub.2Cl.sub.2'		
- 4 Bad<=20011206 and 'silicon oxide' same 'SiH.sub.4' same 'N.sub.20' same 'USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	i				
SiH.sub.4' same 'N.sub.20' same		1	0-d (20011206 and trillian and the trans-		2002/06/10
SiH.sub.2Cl.sub.2'	-	4	• · · · · · · · · · · · · · · · · · ·	- •	1
DERWENT; IBM_TDB USPAT;					10:37
TBM_TDB			51n.sub.201.sub.2		
- 5					
Comparison of the comparison	_	5	//"6127255") or /"5811316") or		2003/06/19
- 27 @ad<=20011206 and 'dioxide' same 'silane' same 'nitrous oxide' same 'silane' same 'nitrous oxide' same 'silane' US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT 2003/06/19 15:06 - 1 "5506178".PN. USPAT 2003/06/19 15:06 - 45 hisatomi-kiyoshi.in. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IS:28					
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB			() (
- 27 @ad<=20011206 and 'dioxide' same 'silane' same 'nitrous oxide' same 'silane' uspat; uspa					
- 27 @ad<=20011206 and 'dioxide' same 'silane' same 'nitrous oxide' same 'silane' US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
Same 'nitrous oxide' same	-	27	<pre>@ad<=20011206 and 'dioxide' same 'silane'</pre>	_	2003/06/20
dichlorosilane'			•		
DERWENT; IBM_TDB USPAT; with 'nitride' with 'SiON' with 'oxide') and memory 1 "5506178".PN. 1 "5506178".PN. 2003/06/19 USPAT IBM_TDB USPAT 1 USPAT 2003/06/19 15:20 15:28					
- 160 (@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide') uS-PGPUB; and memory EFO; JPO; DERWENT; IBM_TDB USPAT 2003/06/19 - 1 "5506178".PN. USPAT 2003/06/19 - 45 hisatomi-kiyoshi.in. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 11:26 - 20 toshiba.as. and 'ONO' and 'oxynitride' US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 15:28					
with 'nitride' with 'SiON' with 'oxide') and memory - 1 "5506178".PN. - 45 hisatomi-kiyoshi.in. - 20 toshiba.as. and 'ONO' and 'oxynitride' - 30 toshiba.as. and 'ONO' and 'oxynitride' - 45 toshiba.as. and 'ONO' and 'oxynitride' - 50 toshiba.as. and 'ONO' and 'oxynitride' - 51 toshiba.as. and 'ONO' and 'oxynitride' - 52 toshiba.as. and 'ONO' and 'oxynitride' - 53 toshiba.as. and 'ONO' and 'oxynitride' - 54 toshiba.as. and 'ONO' and 'oxynitride' - 55 toshiba.as. and 'ONO' and 'oxynitride' - 56 toshiba.as. and 'ONO' and 'oxynitride' - 57 toshiba.as. and 'ONO' and 'oxynitride' - 58 toshiba.as. and 'ONO' and 'oxynitride' - 68 toshiba.as. and 'ONO' and 'oxynitride' - 78 toshiba				IBM_TDB	
with 'nitride' with 'SiON' with 'oxide') and memory - 1 "5506178".PN. - 45 hisatomi-kiyoshi.in. - 20 toshiba.as. and 'ONO' and 'oxynitride' - 30 toshiba.as. and 'ONO' and 'oxynitride' - 45 toshiba.as. and 'ONO' and 'oxynitride' - 50 toshiba.as. and 'ONO' and 'oxynitride' - 51 toshiba.as. and 'ONO' and 'oxynitride' - 52 toshiba.as. and 'ONO' and 'oxynitride' - 53 toshiba.as. and 'ONO' and 'oxynitride' - 54 toshiba.as. and 'ONO' and 'oxynitride' - 55 toshiba.as. and 'ONO' and 'oxynitride' - 56 toshiba.as. and 'ONO' and 'oxynitride' - 57 toshiba.as. and 'ONO' and 'oxynitride' - 58 toshiba.as. and 'ONO' and 'oxynitride' - 68 toshiba.as. and 'ONO' and 'oxynitride' - 78 toshiba	-	160	(@ad<=20011206 and 'oxide' with 'SiON'	_	2003/06/19
DERWENT; IBM_TDB USPAT 45 hisatomi-kiyoshi.in. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB				US-PGPUB;	15:20
- 1 "5506178".PN.			and memory	EPO; JPO;	
-					
- 45 hisatomi-kiyoshi.in.				_	
- 45 hisatomi-kiyoshi.in. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-PGPUB; IS-PGPUB; EPO; JPO; DERWENT; IBM_TDB 15:28	-	1	"5506178".PN.	USPAT	I I
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB			, , , , , , , , , , , , , , , , , , ,		
EPO; JPO; DERWENT; IBM_TDB 20 toshiba.as. and 'ONO' and 'oxynitride' USPAT; 2003/06/19 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	-	45	nisatomi-kiyoshi.in.	· ·	
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					11:26
- 20 toshiba.as. and 'ONO' and 'oxynitride' USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB					
- 20 toshiba.as. and 'ONO' and 'oxynitride' USPAT; 2003/06/19 US-PGPUB; EPO; JPO; DERWENT; IBM TDB					
US-PGPUB; 15:28 EPO; JPO; DERWENT; IBM TDB]	tankih an and toxot at the desired		1 2002 (06 (10
EPO; JPO; DERWENT; IBM TDB	-	20	toshipa.as. and 'ONO' and 'oxynitride'		
DERWENT; IBM TDB					12:58
IBM TDB					
]				
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	T			T
-	341	toshiba.as. and 'oxynitride'	USPAT;	2003/06/19
			US-PGPUB;	15:29
			EPO; JPO;	
			DERWENT;	
	1.0	0.44 00011006	IBM_TDB	
_	16	@ad<=20011206 and 'silicon oxynitride'	USPAT;	2003/06/20
		same 'silane' same 'dichlorosilane'	US-PGPUB;	09:09
			EPO; JPO;	
			DERWENT;	
_	2	@ad<=20011206 and 'SiON' same 'silane'	IBM_TDB	2002/06/20
-		same 'dichlorosilane'	USPAT; US-PGPUB;	2003/06/20
		Same dichiologitane	EPO; JPO;	09:07
			DERWENT;	
			IBM TDB	
_	45	hisatomi-kiyoshi.in.	USPAT;	2003/11/24
		nii da	US-PGPUB;	11:26
			EPO; JPO;	111.20
			DERWENT;]
			IBM TDB	
_	0	@ad<=20011206 and 'oxide' adj2 'SiON'	USPAT;	2003/11/24
		adj2 'nitride' adj2 'SiON' adj2 'oxide'	US-PGPUB;	11:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12	• • • • • • • • • • • • • • • • • • • •	USPĀT;	2003/11/24
		layer'	US-PGPUB;	11:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	296		USPAT;	2003/11/24
		layer'	US-PGPUB;	11:37
			EPO; JPO;	
			DERWENT;	
l_	271	@ad<=20011206 and 'multi' adj2	IBM_TDB USPAT;	2003/11/24
	2/1	'dielectric' and 'memory'	US-PGPUB;	11:46
		diciectic and memory	EPO; JPO;	11.40
			DERWENT;	
			IBM TDB	
-	19	@ad<=20011206 and 'multi' adj1	USPAT;	2003/11/24
		'dielectric' same 'memory'	US-PGPUB;	11:46
	1	·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	34		USPAT;	2003/11/24
		'dielectric' and 'memory'	US-PGPUB;	11:48
			EPO; JPO;	
			DERWENT;	
	100	0-4 (-20011200 / /257 /204)	IBM_TDB	2003/11/24
-	496	@ad<=20011206 and (257/324).ccls.	USPAT;	2003/11/24
			US-PGPUB;	11:51
	[EPO; JPO; DERWENT;	
			IBM TDB	
_	134	@ad<=20011206 and (438/216).ccls.	USPAT;	2003/11/24
1	124	Gad	US-PGPUB;	13:55
1			EPO; JPO;	-0.00
			DERWENT;	
			IBM TDB	
-	147	@ad<=20011206 and (438/621).ccls.	USPAT;	2003/11/24
i -		,,	US-PGPUB;	11:52
			EPO; JPO;	
			DERWENT;	j l
L	L		IBM_TDB	
				